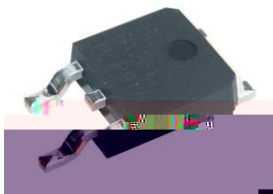
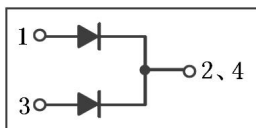


TO-252

Ultrafast Recovery Diode in a TO-252 Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 Anode

PIN 2 4 Cathode

PIN 3 Anode

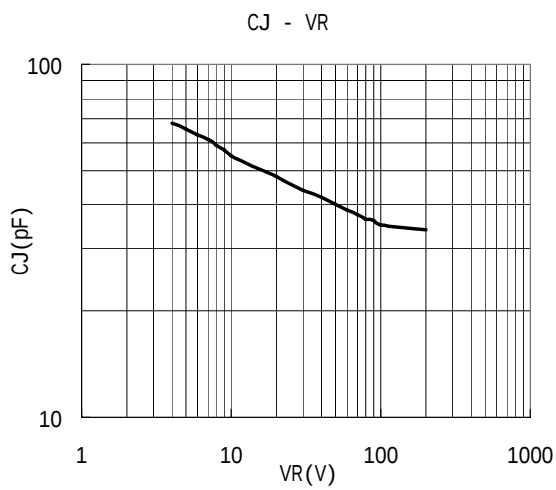
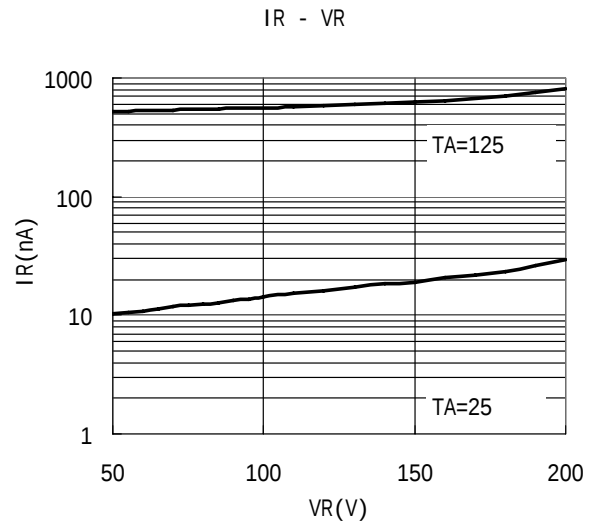
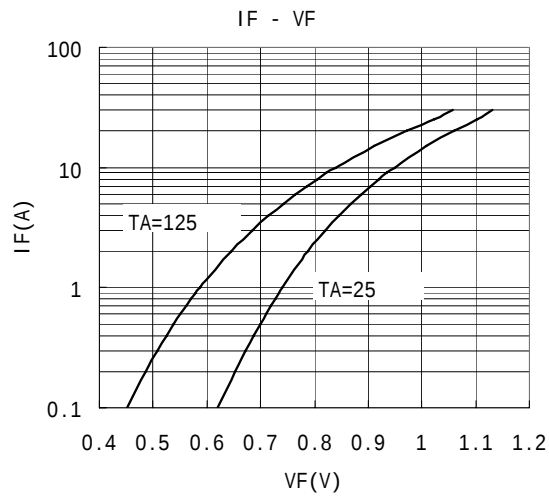
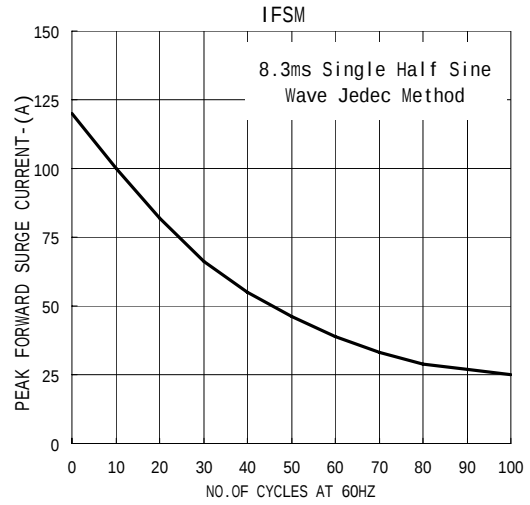
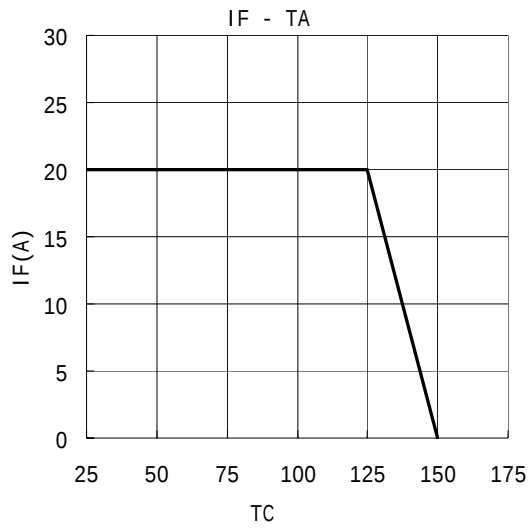
See Marking Instructions.

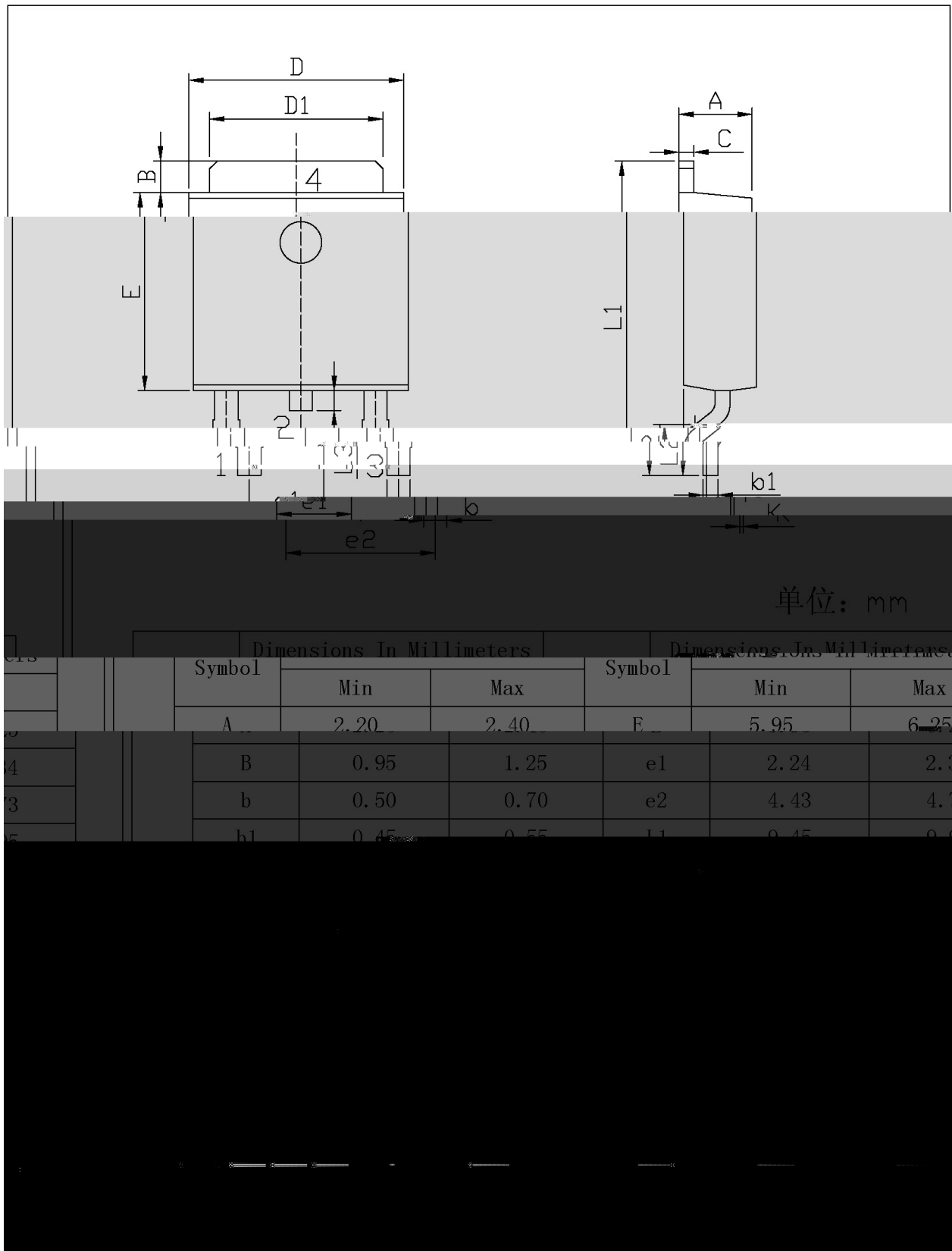
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Forward Current	I_F	2×10	A
Non Repetitive Peak Surge Current	I_{FSM}	120	A
Thermal Resistance Junction to Case	R_{JC}	2.8	/W
Operating and Storage Temperature Range	T_j T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=2A$ $T_c=25$		0.79		V
		$I_F=2A$ $T_c=125$		0.65		V
		$I_F=10A$ $T_c=25$		0.95	1.0	V
		$I_F=10A$ $T_c=125$		0.84	0.9	V
Instantaneous Reverse Current	I_R Note 1	$V_R=200V$ $T_a=25$			10	A
		$V_R=200V$ $T_a=125$			150	A
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_R=1.0A$ $I_{RR}=0.25A$			35	ns

/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip







BR

MURD2020

CT:

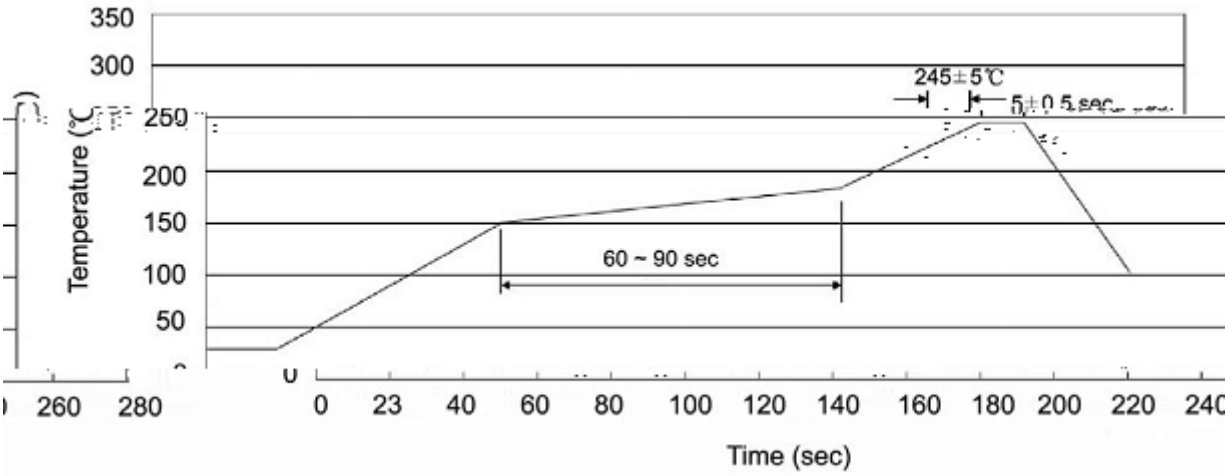
Note:

BR: Company Code

MURD2020 Product Type.

CT: Internal Structure

****: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type		Units 包装数量		Dimension 包装尺寸 (unit: mm ³)	
封装形式	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box	Inner Boxes/Outer Box